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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Koichi KOKUBUN

SERIAL NUMBER: 10/645,529

GROUP: 2814

FILED: August 22, 2003

EXAMINER: PHAM, HOAI V.

FOR: METHOD OF MANUFACTURING THE SEMICONDUCTOR DEVICE HAVING A  
CAPACITOR FORMED IN SOI SUBSTRATE

**REQUEST TO CORRECT TITLE OF INVENTION**

MAIL STOP ISSUE FEE  
COMMISSIONER FOR PATENTS  
P.O. BOX 1450  
ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request  
correction of your records to reflect the correct title of the invention. The title of the  
invention should read as follows: METHOD OF MANUFACTURING THE  
SEMICONDUCTOR **DEVICE** HAVING A CAPACITOR FORMED IN SOI  
SUBSTRATE.

Respectfully Submitted,

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